

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for hermetically packaging a filter including the steps of providing a first wafer (1;27) bearing a plurality of bulk acoustic resonators (BARs) (2;28), providing a second wafer (8;30) having a plurality of wells (9;32), bonding the first and second wafers (1,8;27,30) to each other to form a composite wafer (1,8;36) in which the BARs (2;28) of the first wafer (1;27) are aligned with the wells (9;32) of the second wafer (8;30), and separating individual filters (2;28).

2. (Currently Amended) A method for hermetically packaging electric filters comprising a plurality of thin film bulk acoustic resonators (FBARs) where each resonator (2;28) is made up of a thin piezoelectric layer (2;19) sandwiched between two metal electrodes (4,5;20,21) and other layers of materials, by which the first wafer (1;27) bearing a plurality of such FBAR filters (2;28) is bonded to at least one other wafer (8;30), into which wells (9;32) have previously been etched in the face to be bonded to the face of the first wafer (1;27) bearing the FBAR filters (2;28), said pair of wafers (1,8;27,30) forming a composite wafer (1,8;36), said wells being aligned with said FBAR filters, the individual filters (2;28) being separated after the wafers (1,8;27,30) have been processed.

3. (Currently Amended) A method as claimed in claim 1 wherein holes (12;39) are etched and filled with metal (13;40) to allow contacts to be made to the filters (2;28).

4. (Currently Amended) A method as claimed in claim 1 wherein metal layers (44) are deposited on the edges of the filters (28) after they have been separated in order to allow contacts to be made to the filters.

5. (Currently Amended) A method as claimed in claim 1 wherein a third wafer (14;34) is bonded to the first wafer (1;27) on that face remote from the second wafer (8;30).

6. (Presently Presented) A method as claimed in claim 1 wherein one or more of the wafer bonding processes is undertaken under a vacuum.

7. (Presently Presented) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used is anodic bonding employing a borosilicate bonding layer.

8. (Currently Amended) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used employs a ~~low-melting-point~~ glass as the bonding layer and the bond is made by a combination of heat and pressure.

9. (Presently Presented) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used employs a metal or alloy as the bonding layer and the bond is made by a combination of heat and pressure.

10. (Presently Presented) A filter made by the method according to claim 1.

11. (Original) A filter according to claim 10 comprising an FBAR filter.

12. (Original) A filter according to claim 11 wherein each FBAR filter comprises a plurality of layers consisting of (from lower to upper): a substrate, a dielectric layer, one or more metal layers acting as a lower electrode, a piezoelectric layer, and one or more metal layers acting as an upper electrode.

13. (Original) A filter according to claim 12 wherein each FBAR filter further comprises a top layer which can be either a conductor or an insulator.

14. (Original) A filter according to claim 10 comprising an SBAR filter.